



Materials Research Overview

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13 April 2016



Fundamental research for scientific discovery and innovation to provide superior materials and devices needed for lasting strategic land power dominance

Manufacturing Science

- Advanced & Additive Manufacturing
- Polymer Coatings
- Corrosion & Fatigue
- Energy Coupled-to-Matter



Biological and Bio-inspired

- Materials from Biology
- Technology from Biological Systems
- Characterization and Sensors

Structural

- Advanced Platform
- Integrated Structural & Energy

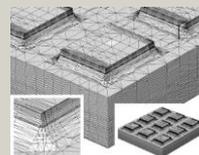
Photonics

- Imaging Sensors & Optics
- Chemical Specific Sensing
- Sensor Protection
- UV Optoelectronic
- High Energy & Tactical Laser
- Quantum Information Science



Electronics

- Nano & 2D
- MEMS
- Flexible & Conformable
- Energy Efficient
- RF Active & Passive

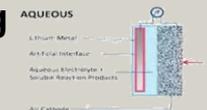


High Strain Rate & Ballistics

- Lightweight & Specialty Metals
- Ceramics & Transparent
- Fabrics & Wearables
- Energy Absorbing
- Composites & Hybrid
- Penetrator & Warhead
- Advanced Mechanics of Materials

Energy & Power

- Energy Storage
- Power Generation & Energy Harvesting
- Fuel Cell
- Thermal Science



**Initial ARL West Materials Research focus:
Energy efficient electronics and semiconductor modeling**



Materials Research: decrease the Size, Weight, Power & Cost of Army technology; reduce logistics burden and enhance survivability, lethality & mobility

Materials for Soldier and Platform Power Systems – Power generation and storage technologies that simultaneously reduce hazards, the logistics tail, and the burden on the Soldier while increasing mission time and effectiveness

Energy-Efficient Electronics and Photonics – Novel materials to reduce the power demand of future Soldier systems

Agile Expedient Manufacturing – Rapid, adaptable production of consumable parts through development of new synthesis and processing capabilities

Quantum Sciences – Materials to exploit quantum phenomena to enable exponential increases in capabilities for command, control, communications, intelligence, surveillance, & reconnaissance

Energy-Coupled-to-Matter for Responsive Materials – Application of high energy fields during materials processing to beneficially alter the resulting material

Lightweight Materials for Army Platforms – Lightweight materials that are stronger than their conventional counterparts to reduce the logistics tail while providing better performance

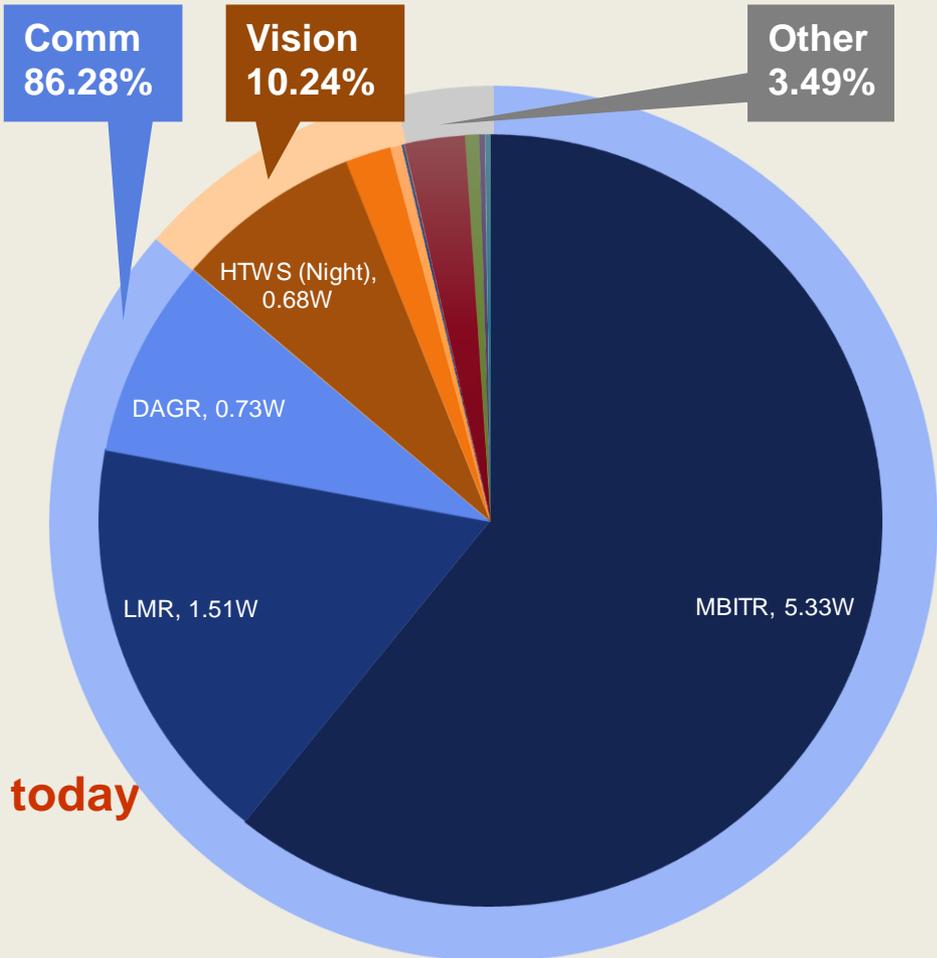


OEF Afghanistan, 72 Hour Mission

<p>AN/PVS 14 (Night Vision) (2) AA .106 lbs/.04 watts*</p> <p>Mark VII (1) 3.9 V lithium .256 lbs/.167 watts*</p> <p>MBITR (8) BB 521 6.4 lbs/5.33 watts*</p> <p>Sure Fire Light (6) CR-123A .222 lbs/.219 watts*</p> <p>Mag Lite (2) AA .106 lbs/.019 watts*</p> <p>DAGR (24) AA & (1) 1/2 AA 1.3 lbs/.729 watts*</p>	<p>Head Set (2) AA .106 lbs/.019 watts*</p> <p>PEQ-2A (2) AA .106 lbs/.011 Watts*</p> <p>HTWS (Night) (12) AA Lithium .384 lbs/.68 watts*</p> <p>M68 CCO (Day) (1) DL 1/3N .007 lbs/.00006 watts*</p> <p>LMR (8) 3600 mAh NIMH 6.4 lbs/1.51 watts*</p> <p>P-Beacon (1) 9V 1 lbs/.049 watts*</p>
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Total: 7 types of batteries.
70 batteries, 16 lbs; 9.16 watts

*Average Watts per 72 hours



7 types, 70 batteries, 16 pounds

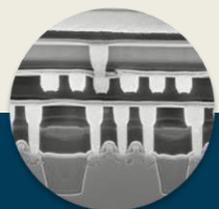
9.16 watts average for 72 hour mission today

Weight is constrained but additional warfighting capabilities are in demand

Efficiency must improve

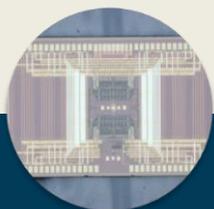


Reduce the battery load on the Soldier by addressing the demand side of the electronics that will underpin the Soldier's future communications, computing, and sensing gear.



Improved materials and devices

- III-V + CMOS
- 2D materials (MoS₂)
- Phase change (GeTe)



Circuits and systems

- All CMOS Front End
- Ultra-Low-Power FPGA
- RF Data Converters
- GeTe RF switches



Heterogeneous integration of efficient devices

- InP on Si
- FPGA-FLEX-ASICs Stack
- GaN on Si



Waveforms and signal processing

- Embedded Processing
- Digital Waveforms
- Waveform parsing to accelerator chiplets

Program goals require improvements across the board



Problem: It now takes more energy to move data than to generate it.

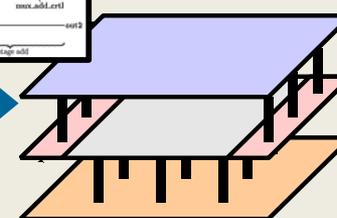
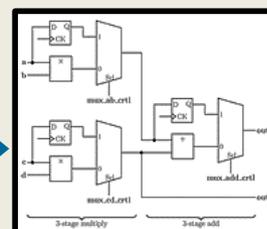
Approach: Increase efficiency by stacking accelerators, FPGAs, & memory.

4,096 point Fast Fourier Transform computation example:

	Tech. node	Power	Efficiency (GFLOPs/W)	Comparison	
				Power	Eff.
1x ULP-FPGA ²	65 nm	0.3 W	28.9	1x	1x
14x Virtex-5 ¹ (Convey HC-1)	65 nm	392 W	0.4	1307x	72x ←
3x Virtex-6 ¹ (Pico M-503)	45 nm	37 W	1.4	123x	21x ←

Improvements from:

- Dedicated flexible accelerators →
- Tight memory integration with application specific memory controller →



Memory
Accelerator
Controller

1. K. S. P. Pereira, "Characterization of FPGA-based high performance computers," Master's thesis, Virginia Polytechnic Institute and State University, 2011.
2. P. Gadfort, A. Dasu, et. al. "A Power Efficient Reconfigurable System-in-Stack: 3D Integration of Accelerators, FPGAs, and DRAM," IEEE SOCC 2014.



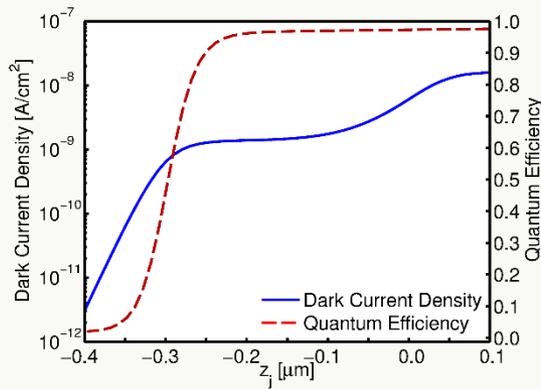
U.S. ARMY
RDECOM

UNCLASSIFIED

Open Campus Center for
Semiconductor Materials Modeling

ARL

A virtual center to bring together government, academia, and industry from across the country to push semiconductor research forward to benefit all partners



Example

Numerically modeled the dark current density and quantum efficiency of a single P⁺-on-n HgCdTe pixel versus junction depth z_j .

Schuster *et al*, Proc. SPIE 9609 (2015)

Schuster *et al*, Appl. Phys. Lett., 118 (2015)

- **Start with HgCdTe: modeling, growth, and characterization from materials to devices to focal-plane arrays**
- **Expand into other IR materials**
- **Broaden scope to other material systems**
- **Share Computational Resources**
 - Pooling of computational tools and resources, (i.e. DoD HPC)
 - Streamlined access to DoD HPC – hours free to ARL collaborators
 - Modeling software: VASP (DFT) for Material Modeling, ANSYS, etc.
- **Establishing virtual center with presence at ARL West**



Models can be used stand-alone or to bridge scales.
Parameters extracted at each level become inputs for next level.

Material Modeling**Device Modeling****System Modeling**

Increasing length scale from atoms-to-systems

1 – 50 Å

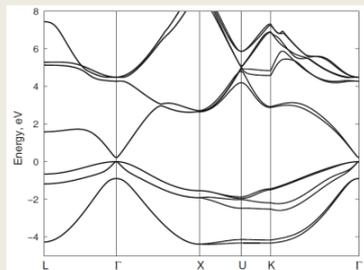
1 – 500 nm

100 nm – 10 µm

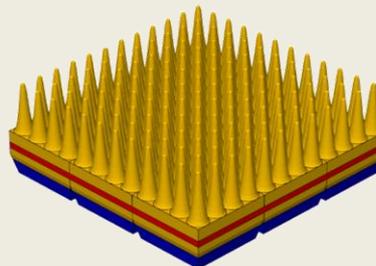
5 – 50 µm

1 – 1000 mm

Feedback to earlier levels for validation

**Material Characteristics:**

- Properties
- Carrier Recombination
- Transport Phenomena

**Device/Array Performance:**

- Geometrical effects
- J(V), SR, QE, MTF
- Crosstalk
- Array MTF

**System Performance:**

- Sensitivity
- Dynamic Range
- Resolution (MTF from detector/lenses, etc.)

The Center will develop new and leverage existing models at every scale.
Validate performance through growth, processing, and characterization

Leveraging the combined capabilities of government, academia, and industry in a collaborative fashion will accelerate semiconductor research to the benefit of all partners



ARL Materials Campaign is pursuing fundamental research for scientific discovery and innovation to provide superior materials and devices needed for lasting strategic land power dominance

To that end, ARL seeks collaboration with West Coast partners to expand research efforts in:

- **Embedded signal processing**
- **Energy-efficient electronics**
- **Multiscale modeling of semiconductor materials and devices**